

# 74HC251; 74HCT251

8-input multiplexer; 3-state

Rev. 3 — 9 July 2013

Product data sheet

## 1. General description

The 74HC251; 74HCT251 is an 8-bit multiplexer with eight binary inputs (I0 to I7), three select inputs (S0 to S2) and an output enable input ( $\overline{OE}$ ). The select inputs select one of the eight binary inputs and route it to the complementary outputs (Y and  $\overline{Y}$ ). A HIGH on  $\overline{OE}$  causes the outputs to assume a high-impedance OFF-state. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of  $V_{CC}$ .

## 2. Features and benefits

- Input levels:
  - ◆ For 74HC251: CMOS level
  - ◆ For 74HCT251: TTL level
- Low-power dissipation
- Non-inverting data path
- Specified in compliance with JEDEC standard no. 7A
- ESD protection:
  - ◆ HBM JESD22-A114F exceeds 2 000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

## 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC251N	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT251N				
74HC251D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT251D				
74HC251DB	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT251DB				
74HC251PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT251PW				

## 4. Functional diagram

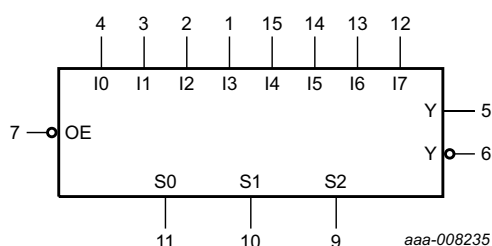


Fig 1. Logic symbol

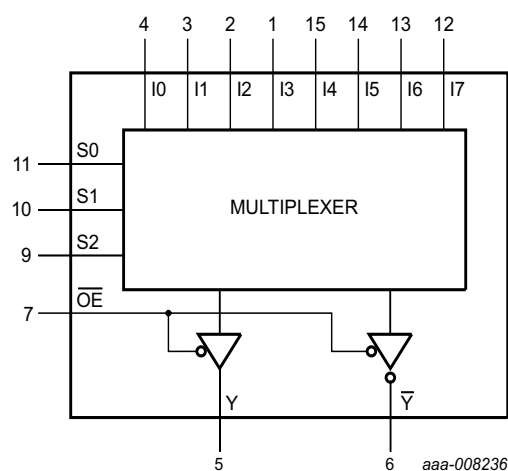


Fig 2. Functional diagram

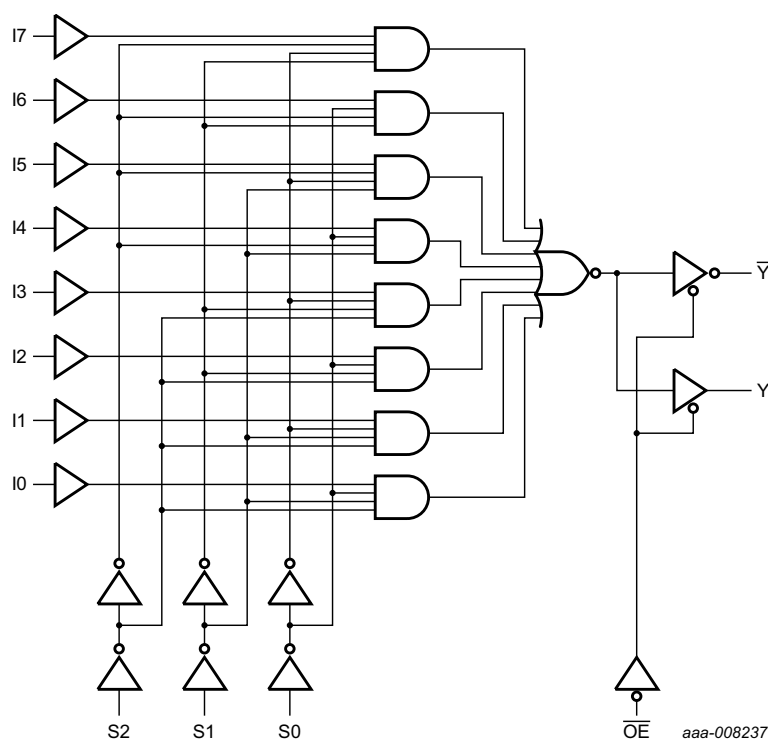


Fig 3. Logic diagram

## 5. Pinning information

### 5.1 Pinning

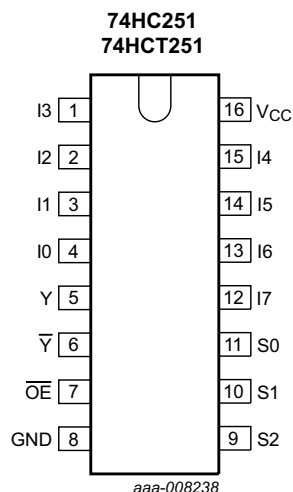


Fig 4. Pin configuration DIP16

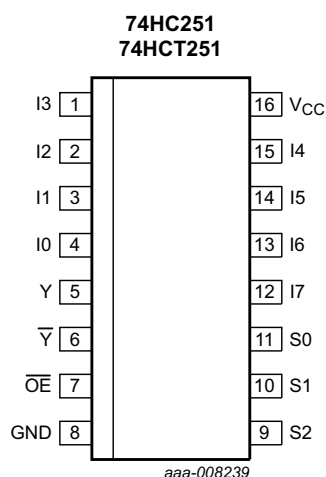


Fig 5. Pin configuration SO16

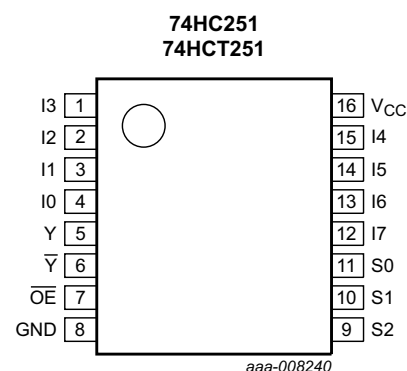


Fig 6. Pin configuration SSOP16 and TSSOP16

### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
I0 to I7	4, 3, 2, 1, 15, 14, 13, 12	data inputs
Y	5	multiplexer output
$\bar{Y}$	6	complementary multiplexer output
$\overline{OE}$	7	output enable input (active LOW)
GND	8	ground (0 V)
S0, S1, S2	11, 10, 9	common data select inputs
V <sub>CC</sub>	16	supply voltage

## 6. Functional description

Table 3. Function table<sup>[1]</sup>

Input												Output	
OE	S2	S1	S0	I0	I1	I2	I3	I4	I5	I6	I7	Y	Y
H	X	X	X	X	X	X	X	X	X	X	X	Z	Z
L	L	L	L	L	X	X	X	X	X	X	X	H	L
L	L	L	L	H	X	X	X	X	X	X	X	L	H
L	L	L	H	X	L	X	X	X	X	X	X	H	L
L	L	L	H	X	H	X	X	X	X	X	X	L	H
L	L	H	L	X	X	L	X	X	X	X	X	H	L
L	L	H	L	X	X	H	X	X	X	X	X	L	H
L	L	H	H	X	X	X	L	X	X	X	X	H	L
L	L	H	H	X	X	X	H	X	X	X	X	L	H
L	H	L	L	X	X	X	X	L	X	X	X	H	L
L	H	L	L	X	X	X	X	H	X	X	X	L	H
L	H	L	H	X	X	X	X	X	L	X	X	H	L
L	H	L	H	X	X	X	X	X	H	X	X	L	H
L	H	H	L	X	X	X	X	X	X	L	X	H	L
L	H	H	L	X	X	X	X	X	X	H	X	L	H
L	H	H	H	X	X	X	X	X	X	X	L	H	L
L	H	H	H	X	X	X	X	X	X	X	H	L	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V or V <sub>I</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < -0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>O</sub>	output current	V <sub>O</sub> = -0.5 V to (V <sub>CC</sub> + 0.5 V)	-	±25	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C

**Table 4.** Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$P_{\text{tot}}$	total power dissipation	$T_{\text{amb}} = -40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$			
	DIP16 package		[1] -	750	mW
	SO16 package		[2] -	500	mW
	(T)SSOP16 package		[3] -	500	mW

[1] For DIP16 package:  $P_{\text{tot}}$  derates linearly with 12 mW/K above 70 °C.[2] For SO16 package:  $P_{\text{tot}}$  derates linearly with 8 mW/K above 70 °C.[3] For SSOP16 and TSSOP16 packages:  $P_{\text{tot}}$  derates linearly with 5.5 mW/K above 60 °C.

## 8. Recommended operating conditions

**Table 5.** Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC251			74HCT251			Unit
			Min	Typ	Max	Min	Typ	Max	
$V_{\text{CC}}$	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
$V_{\text{I}}$	input voltage		0	-	$V_{\text{CC}}$	0	-	$V_{\text{CC}}$	V
$V_{\text{O}}$	output voltage		0	-	$V_{\text{CC}}$	0	-	$V_{\text{CC}}$	V
$T_{\text{amb}}$	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{\text{CC}} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{\text{CC}} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{\text{CC}} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

## 9. Static characteristics

**Table 6. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = −40 °C to +85 °C		T <sub>amb</sub> = −40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC251										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I <sub>O</sub> = −4.0 mA; V <sub>CC</sub> = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I <sub>O</sub> = −5.2 mA; V <sub>CC</sub> = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I <sub>O</sub> = 5.2 mA; V <sub>CC</sub> = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>OZ</sub>	OFF-state output current	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>O</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	±0.5	-	±5.0	-	±10.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	8.0	-	80	-	160	μA
C <sub>I</sub>	input capacitance		-	3.5	-					pF

**Table 6. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = –40 °C to +85 °C		T <sub>amb</sub> = –40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT251										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = –20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = –4 mA	3.98	4.32	-	3.84	-	3.7	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>OZ</sub>	OFF-state output current	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 5.5 V; V <sub>O</sub> = V <sub>CC</sub> or GND per input pin; other inputs at V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A	-	-	±0.5	-	±5.0	-	±10	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	8.0	-	80	-	160	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> – 2.1 V; other inputs at V <sub>CC</sub> or GND; V <sub>CC</sub> = 4.5 V to 5.5 V; I <sub>O</sub> = 0 A								
		per input pin; I <sub>n</sub> inputs	-	100	360	-	450	-	490	μA
		per input pin; $\overline{\text{OE}}$ input	-	150	540	-	675	-	735	μA
		per input pin; S <sub>n</sub> input	-	150	540	-	675	-	735	μA
C <sub>I</sub>	input capacitance		-	3.5	-					pF

## 10. Dynamic characteristics

**Table 7. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V);  $C_L = 50$  pF unless otherwise specified; for test circuit, see [Figure 10](#).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = −40 °C to +85 °C		T <sub>amb</sub> = −40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC251										
t <sub>pd</sub>	propagation delay	In to Y; see <a href="#">Figure 7</a>	[1]							
		V <sub>CC</sub> = 2.0 V	-	50	170	-	215	-	255	ns
		V <sub>CC</sub> = 4.5 V	-	18	34	-	43	-	51	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	15	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	14	29	-	37	-	43	ns
		In to $\bar{Y}$ ; see <a href="#">Figure 7</a>	[1]							
		V <sub>CC</sub> = 2.0 V	-	55	175	-	220	-	265	ns
		V <sub>CC</sub> = 4.5 V	-	20	35	-	44	-	53	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	17	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	16	30	-	37	-	45	ns
		Sn to Y; see <a href="#">Figure 8</a>	[1]							
		V <sub>CC</sub> = 2.0 V	-	66	205	-	255	-	310	ns
		V <sub>CC</sub> = 4.5 V	-	24	41	-	51	-	62	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	20	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	19	35	-	43	-	53	ns
		Sn to $\bar{Y}$ ; see <a href="#">Figure 8</a>	[1]							
		V <sub>CC</sub> = 2.0 V	-	69	205	-	255	-	310	ns
		V <sub>CC</sub> = 4.5 V	-	25	41	-	51	-	62	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	21	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	20	35	-	43	-	53	ns
t <sub>en</sub>	enable time	$\overline{OE}$ to Y, $\bar{Y}$ ; see <a href="#">Figure 8</a>	[2]							
		V <sub>CC</sub> = 2.0 V	-	36	140	-	175	-	210	ns
		V <sub>CC</sub> = 4.5 V	-	13	28	-	35	-	42	ns
		V <sub>CC</sub> = 6.0 V	-	10	24	-	30	-	36	ns
t <sub>dis</sub>	disable time	$\overline{OE}$ to Y, $\bar{Y}$ ; see <a href="#">Figure 8</a>	[3]							
		V <sub>CC</sub> = 2.0 V	-	39	140	-	170	-	210	ns
		V <sub>CC</sub> = 4.5 V	-	14	28	-	35	-	42	ns
		V <sub>CC</sub> = 6.0 V	-	11	24	-	30	-	36	ns
t <sub>t</sub>	transition time	Y, $\bar{Y}$ ; see <a href="#">Figure 7</a>	[4]							
		V <sub>CC</sub> = 2.0 V	-	19	75	-	95	-	110	ns
		V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns
		V <sub>CC</sub> = 6.0 V	-	6	13	-	16	-	19	ns
C <sub>PD</sub>	power dissipation capacitance	C <sub>L</sub> = 50 pF; f = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub>	[5]	-	44	-	-	-	-	pF



**Table 7. Dynamic characteristics ...continued**

Voltages are referenced to GND (ground = 0 V);  $C_L = 50$  pF unless otherwise specified; for test circuit, see [Figure 10](#).

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = −40 °C to +85 °C		T <sub>amb</sub> = −40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT251										
t <sub>pd</sub>	propagation delay	In to Y; see <a href="#">Figure 7</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 4.5 V	-	22	35	-	44	-	53	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	19	-	-	-	-	-	ns
		In to $\overline{Y}$ ; see <a href="#">Figure 7</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 4.5 V	-	22	35	-	44	-	53	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	19	-	-	-	-	-	ns
		Sn to Y; see <a href="#">Figure 8</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 4.5 V	-	24	44	-	55	-	66	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	20	-	-	-	-	-	ns
		Sn to $\overline{Y}$ ; see <a href="#">Figure 8</a> <a href="#">[1]</a>								
		V <sub>CC</sub> = 4.5 V	-	25	44	-	55	-	66	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	21	-	-	-	-	-	ns
t <sub>en</sub>	enable time	$\overline{OE}$ to Y, $\overline{Y}$ ; see <a href="#">Figure 8</a> <a href="#">[2]</a>								
		V <sub>CC</sub> = 4.5 V	-	13	28	-	35	-	42	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	13	-	-	-	-	-	ns
t <sub>dis</sub>	disable time	$\overline{OE}$ to Y, $\overline{Y}$ ; see <a href="#">Figure 8</a> <a href="#">[3]</a>								
		V <sub>CC</sub> = 4.5 V	-	14	28	-	35	-	42	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	18	-	-	-	-	-	ns
t <sub>t</sub>	transition time	Y, $\overline{Y}$ ; see <a href="#">Figure 7</a> <a href="#">[4]</a>								
		V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns
C <sub>PD</sub>	power dissipation capacitance	C <sub>L</sub> = 50 pF; f = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> <a href="#">[5]</a>	-	46	-	-	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2]  $t_{en}$  is the same as  $t_{PZH}$  and  $t_{PZL}$ .

[3]  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ .

[4]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .

[5]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu\text{W}$ ).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:

$f_i$  = input frequency in MHz;

$f_o$  = output frequency in MHz;

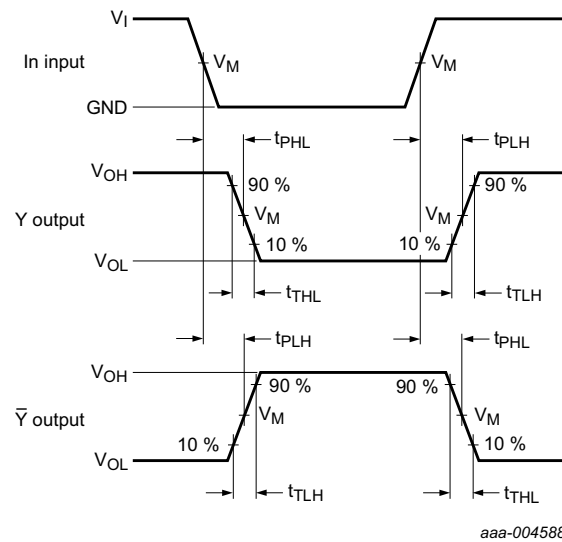
$C_L$  = output load capacitance in pF;

$V_{CC}$  = supply voltage in V;

$N$  = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

## 11. Waveforms

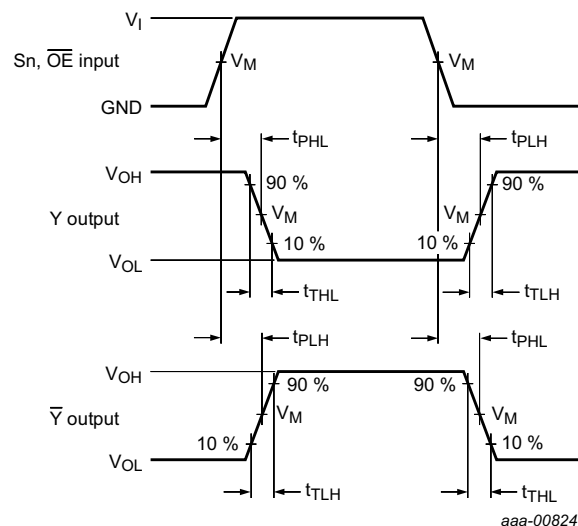


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Measurement points are given in [Table 8](#).

$V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 7. Propagation delay input (In) to output (Y,  $\bar{Y}$ ) and the output (Y,  $\bar{Y}$ ) transition time**

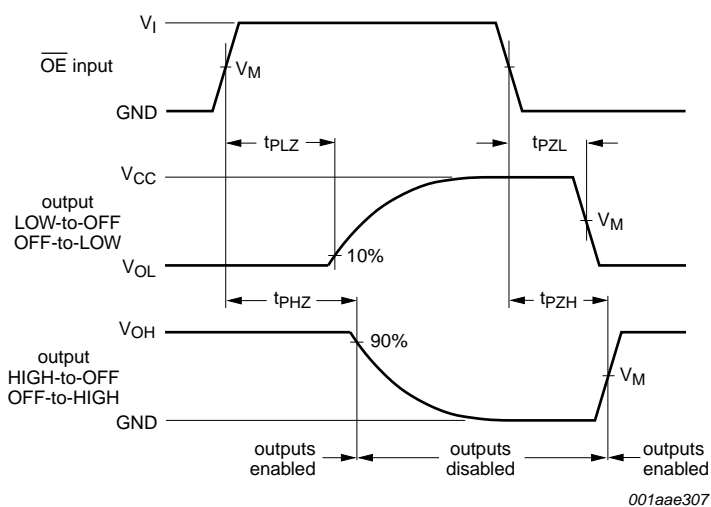


aaa-008241

Measurement points are given in [Table 8](#).

$V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 8. Propagation delay input (Sn,  $\overline{OE}$ ) to output (Y,  $\bar{Y}$ )**



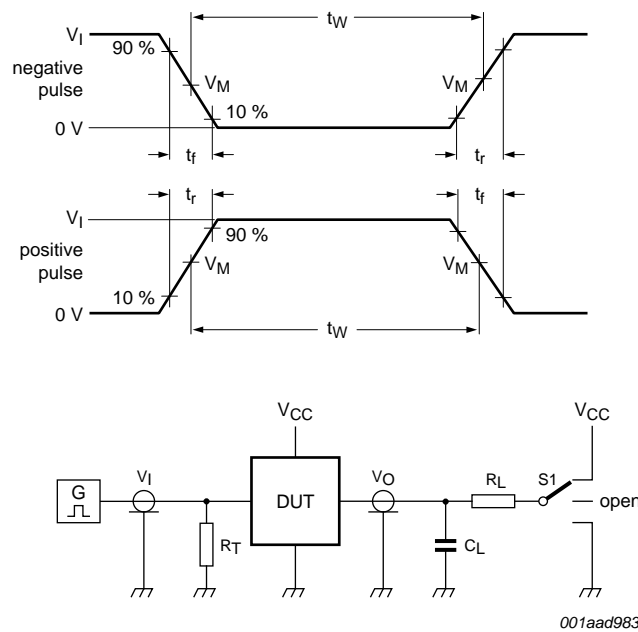
Measurement points are given in [Table 8](#).

$V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 9. Enable and disable times**

**Table 8. Measurement points**

Type	Input	Output
	$V_M$	$V_M$
74HC251	$0.5V_{CC}$	$0.5V_{CC}$
74HCT251	1.3 V	1.3 V



Test data is given in [Table 9](#).

Definitions test circuit:

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_L$  = Load resistance.

S1 = Test selection switch.

**Fig 10. Test circuit for measuring switching times**

**Table 9. Test data**

Type	Input		Load		S1 position		
	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
74HC251	$V_{CC}$	6 ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$
74HCT251	3 V	6 ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$

## 12. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4

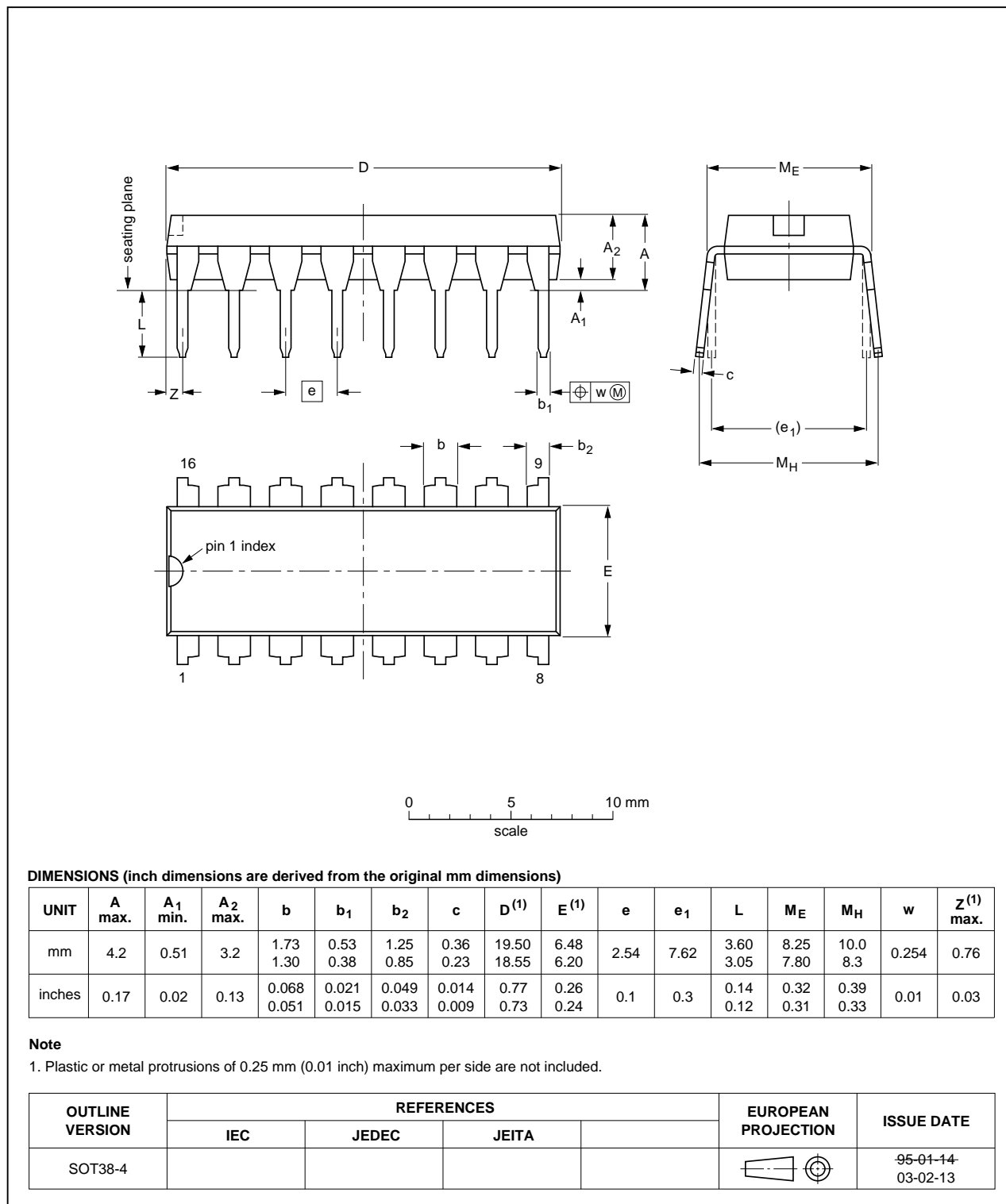


Fig 11. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

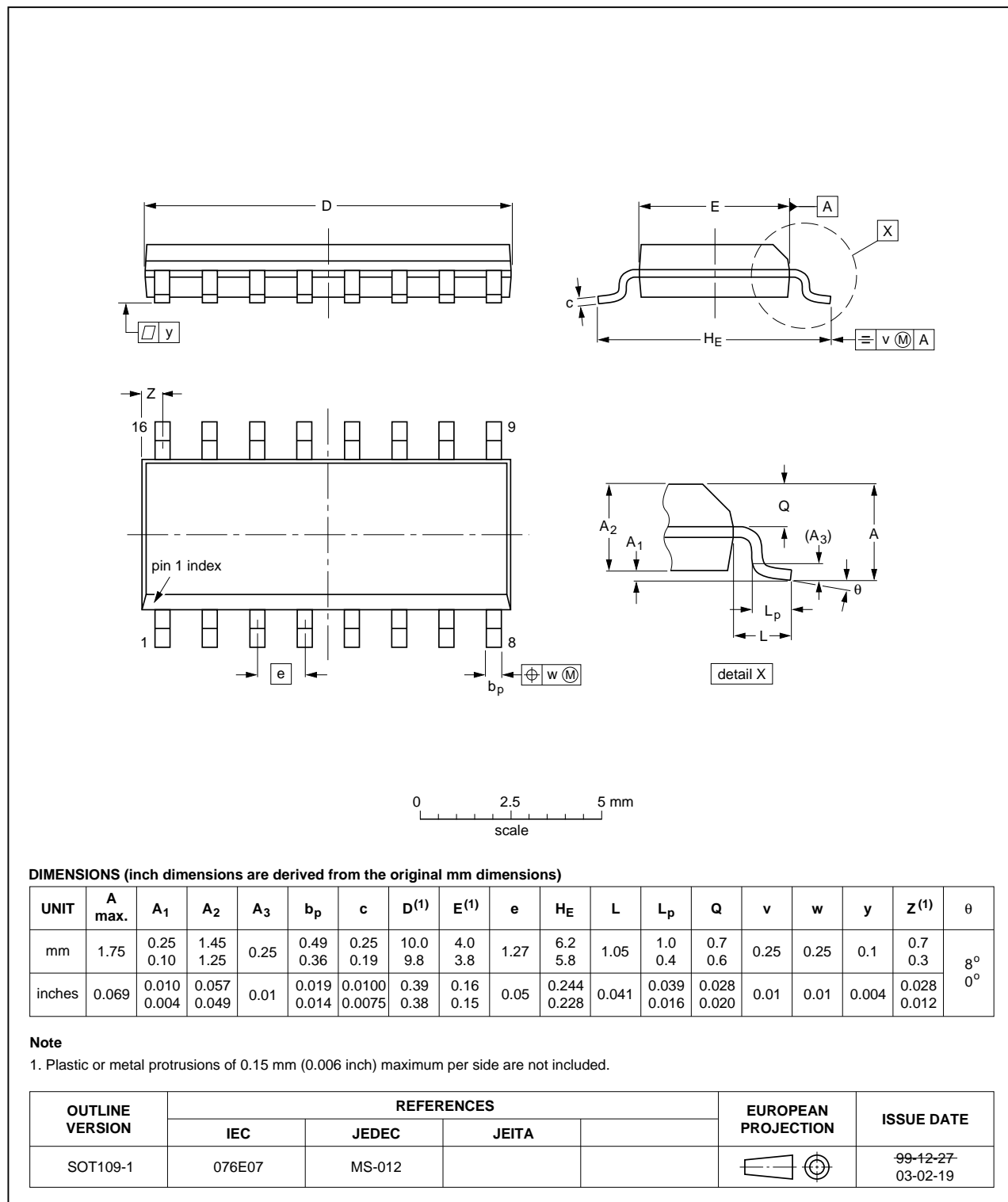


Fig 12. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

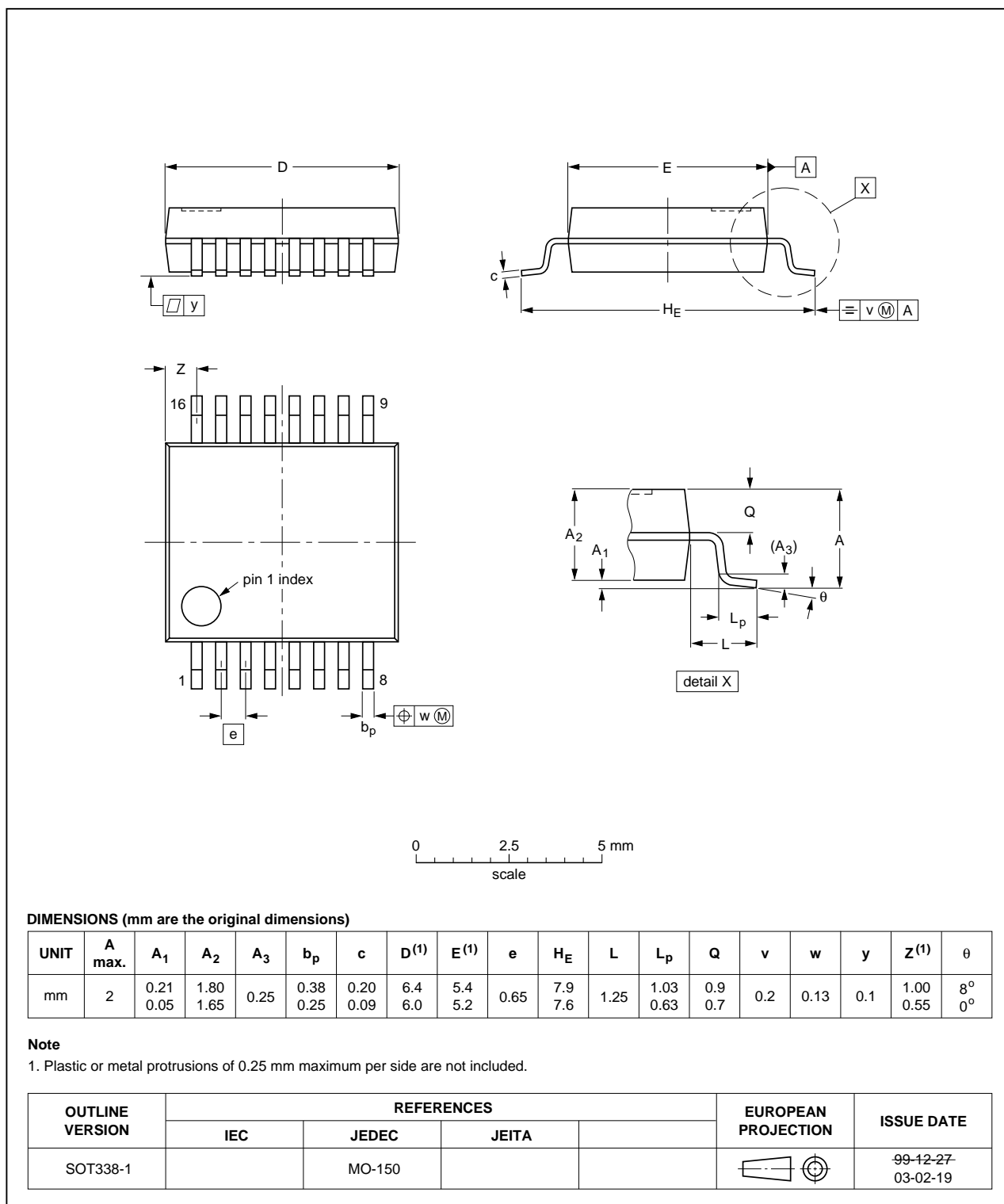
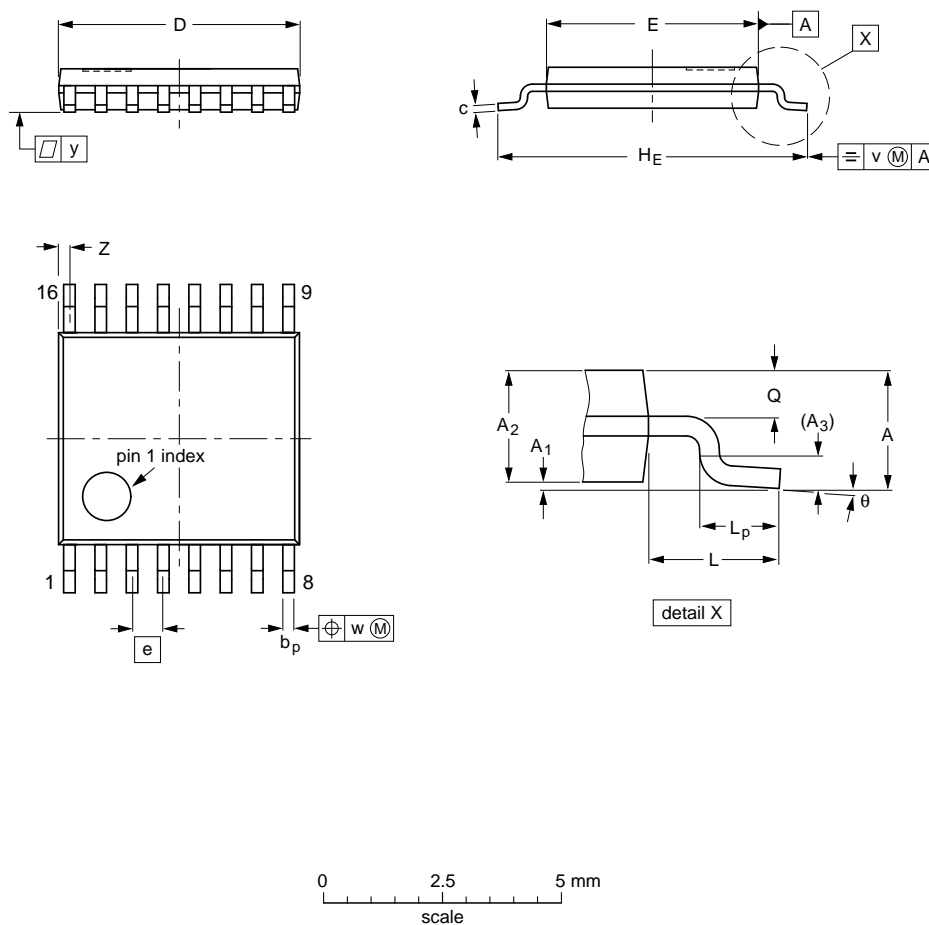


Fig 13. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



**DIMENSIONS** (mm are the original dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(2)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

**Notes**

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				99-12-27 03-02-18

Fig 14. Package outline SOT403-1 (TSSOP16)



## 13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

## 14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT251 v.3	20130709	Product data sheet	-	74HC_HCT251_CNV v.2
Modifications:	<ul style="list-style-type: none"><li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>Legal texts have been adapted to the new company name where appropriate.</li></ul>			
74HC_HCT251_CNV v.2	19970828	Product specification	-	

## 15. Legal information

### 15.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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